UNIKC Semiconductor

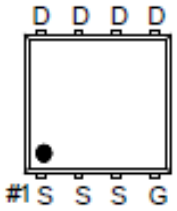
RoHS Compliant

P2003BE

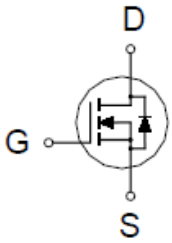
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	20mΩ @V_{GS} = 10V	7A



PDFN 3x3S



ABSOLUTE MAXIMUM RATINGS (T_J = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	T_C = 25 °C	I_D	25	A
	T_C = 100 °C		15	
	T_A = 25 °C		7	
	T_A = 70 °C		5.7	
Pulsed Drain Current[1]		I_{DM}	50	
Avalanche Current		I_{AS}	18	
Avalanche Energy	L = 0.1mH	E_{AS}	16	mJ
Power Dissipation	T_C = 25 °C	P_D	21	W
	T_C = 100 °C		8	
	T_A = 25 °C		1.7	
	T_A = 70 °C		1	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

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THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		75	°C / W
Junction-to-Case	$R_{\theta JC}$		6	

[1]Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.4	2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V , T_J = 55 °C			10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 5V, V_{GS} = 10V	50			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 6A		25	31	mΩ
		V_{GS} = 10V, I_D = 8A		18	20	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 8A		20		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		467		pF
Output Capacitance	C_{oss}			168		
Reverse Transfer Capacitance	C_{rss}			106		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		2.1		Ω
Total Gate Charge[2]	$Q_{g(VGS=10V)}$	V_{DS} = 0.5$V_{(BR)DSS}$, I_D = 15A		11		nC
	$Q_{g(VGS=4.5V)}$			7.5		
Gate-Source Charge[2]	Q_{gs}			3.8		
Gate-Drain Charge[2]	Q_{gd}			3.3		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 15V, $I_D \cong$ 8A, V_{GEN} = 10V, R_G = 6Ω		5		nS
Rise Time[2]	t_r			3.5		
Turn-Off Delay Time[2]	$t_{d(off)}$			25		
Fall Time[2]	t_f			10		

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SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS(T_J = 25 °C)						
Continuous Current	I_S				1.2	A
Forward Voltage[1]	V_{SD}	I_F = 8A, V_{GS} = 0V			1.4	V
Reverse Recovery Time	t_{rr}	I_F = 8A, dI_F/dt = 100A /μs		15		nS
Reverse Recovery Charge	Q_{rr}			18		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

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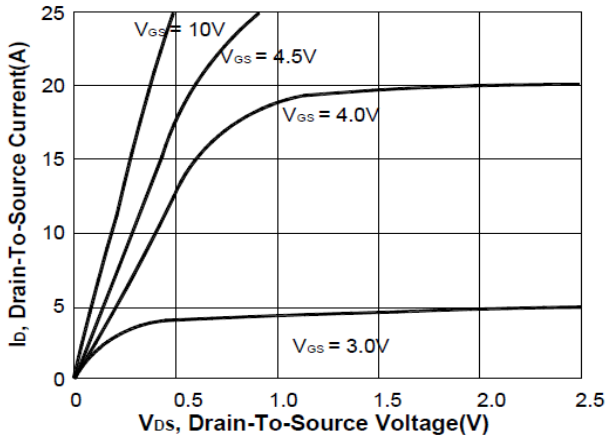
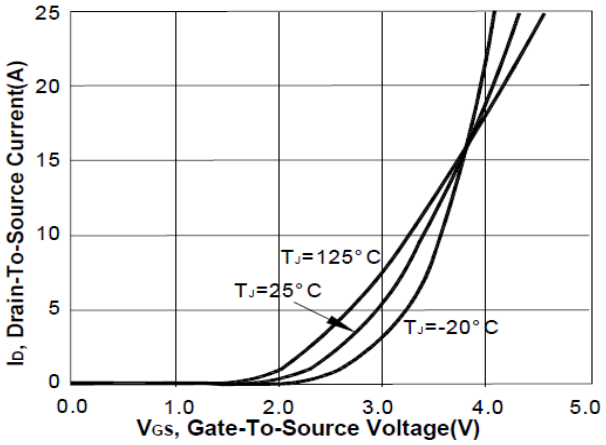
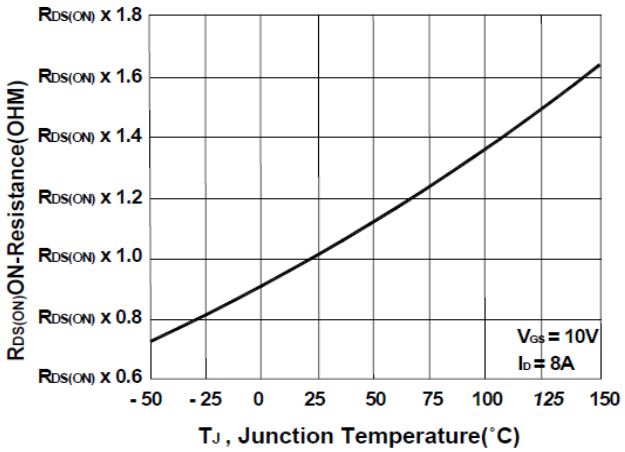
Output Characteristics



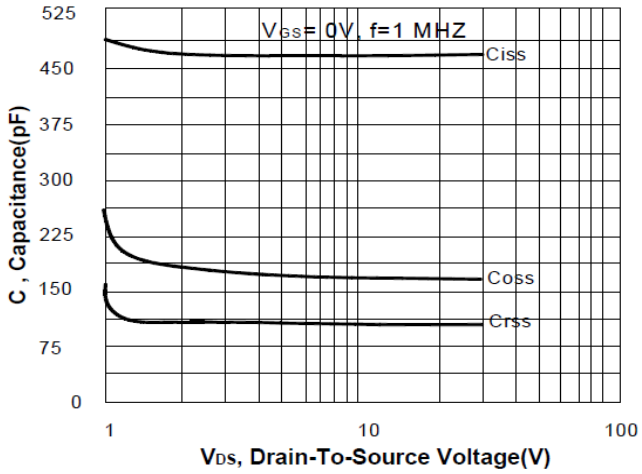
Transfer Characteristics



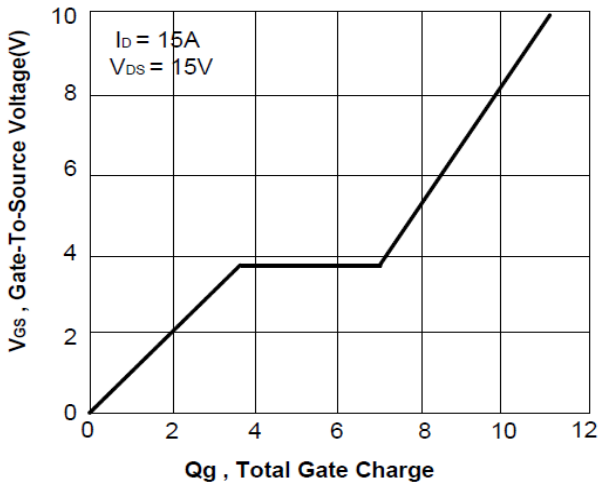
On-Resistance VS Temperature



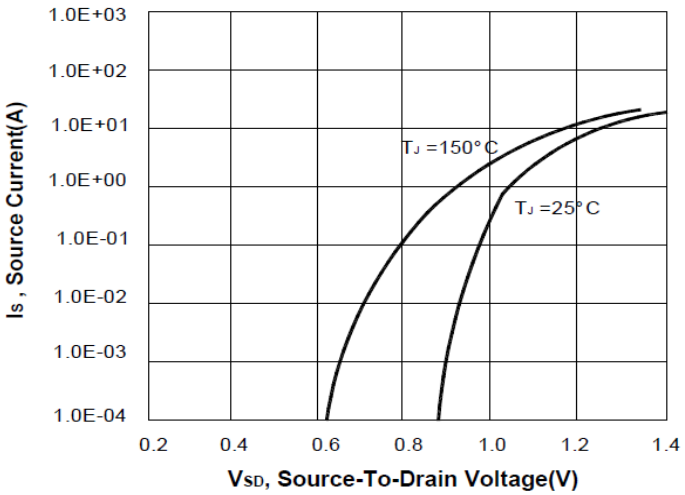
Capacitance Characteristic



Gate charge Characteristics



Source-Drain Diode Forward Voltage



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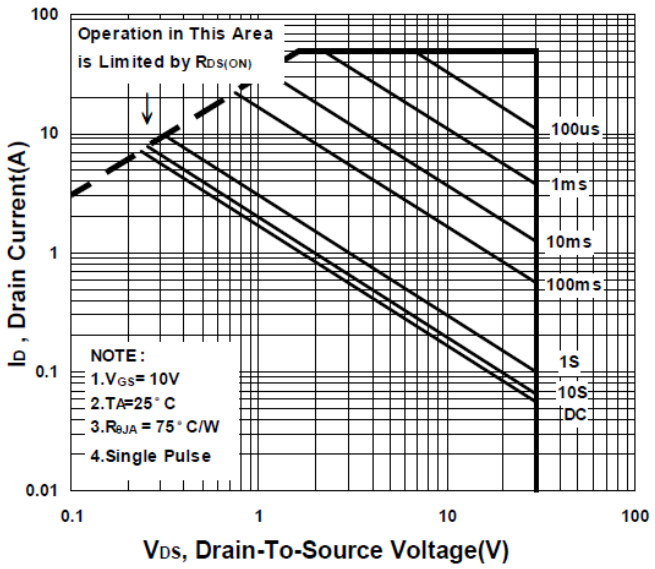
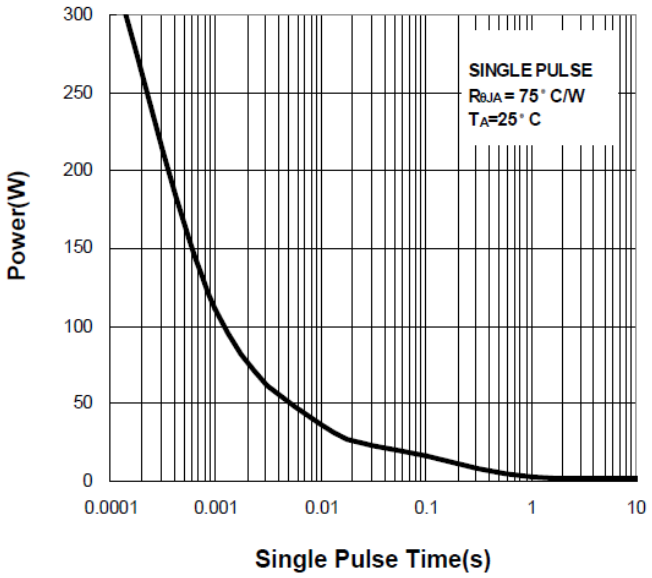
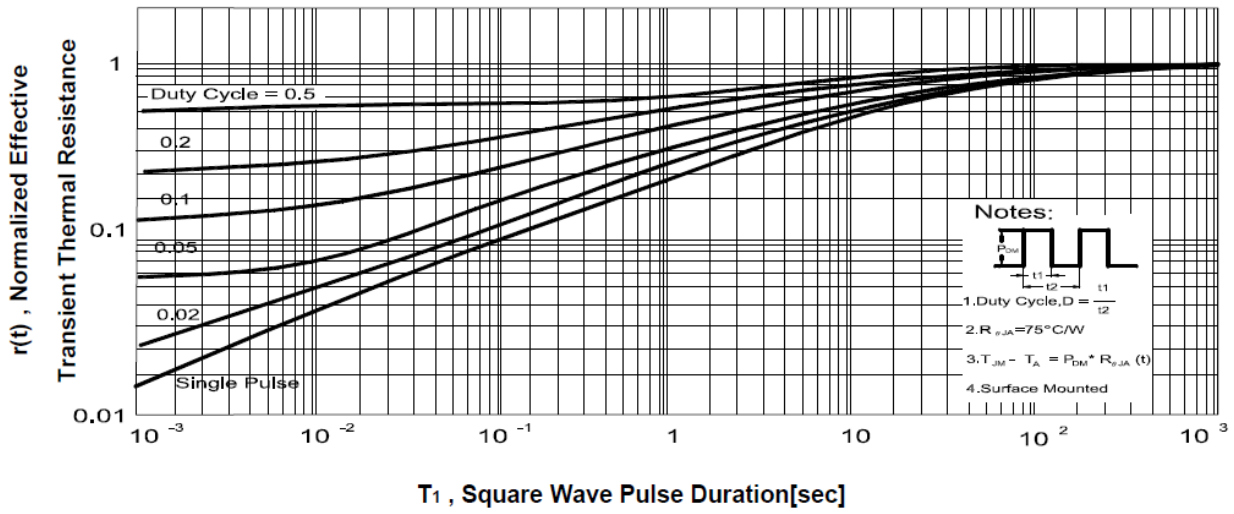
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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Package Dimension

PDFN 3x3S MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	2.9	3.0	3.1	I		0.20	
B	2.35	2.4	2.55	J	0.27	0.35	0.4
C	2.9	3.0	3.1	K		0.45	
D	0.32	0.4	0.45	L	0.7	0.8	0.9
E	2.0	2.1	2.2				
F	0.32	0.42	0.47				
G		0.65					
H	0.27	0.35	0.525